TOLSA

Toulouse Open Laboratory for Semiconductor Analysis

CENTRE NATIONAL D'ÉTUDES SPATIALES

Centres de Compétence Technique

ANADEF

Session 1 : Static Emission microscopy

Chairman Christof Brillert, INFINEON Munich

10:00-10:20	Static Emission microscopy background (Christian Boit, TU Berlin)
10:20-10:40	Use of Static Emission for ESD protection structure analysis (Marise Bafleur, LAAS) (CANCELED)
10:40-11:00	InGaAs versus CCD (Freescale, TOLSA)
11:00-11:20	SIL for improved sensitivity and spatial resolution (Hervé Deslandes, DCGSystems)
11:20-11:40	Best use of SIL: Difference between Aplanatic and Centric SIL, effects of magnification size for the backing objective and the thickness of the Si. (Larry Ross, Semicaps)
11:40-12:00	Influence of Temperature Variation on Electrical and Photon Emission AlGaN/GaN High Mobility Electron Transistors Characterization.(Piotr Laskowski, TU Berlin)
12:00-12:20	Questions and answers (Moderator Bernard Picart, ATMEL Rousset)